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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-WFQFN Exposed Pad
Supplier Device Package	32-HWQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101bcdna-u0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(12/12)

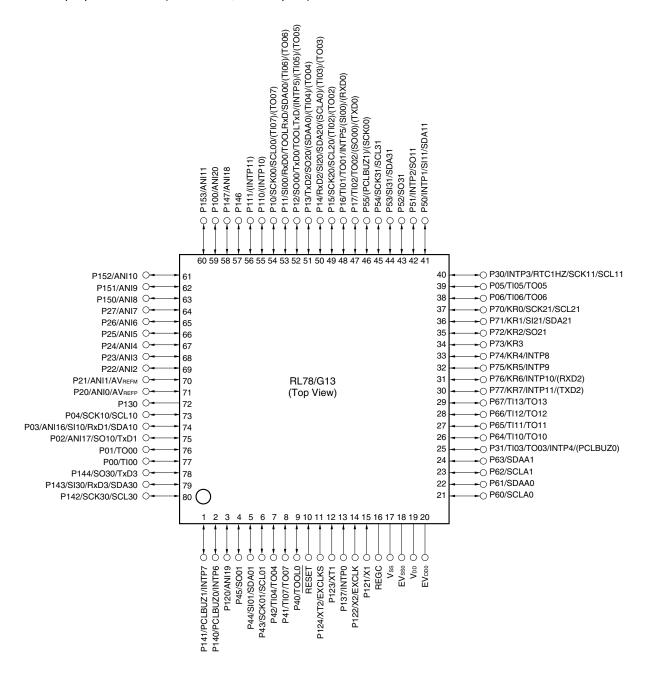
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
128 pins	128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)	Mounted	A D	R5F100SHAFB#V0, R5F100SJAFB#V0, R5F100SKAFB#V0, R5F100SLAFB#V0 R5F100SHAFB#X0, R5F100SJAFB#X0, R5F100SKAFB#X0, R5F100SLAFB#X0 R5F100SHDFB#V0, R5F100SJDFB#V0, R5F100SKDFB#V0, R5F100SLDFB#V0 R5F100SHDFB#X0, R5F100SJDFB#X0, R5F100SKDFB#X0, R5F100SLDFB#X0
		Not mounted	A D	R5F101SHAFB#V0, R5F101SJAFB#V0, R5F101SKAFB#V0, R5F101SLAFB#V0 R5F101SHAFB#X0, R5F101SJAFB#X0, R5F101SKAFB#X0, R5F101SLAFB#X0 R5F101SHDFB#V0, R5F101SJDFB#V0, R5F101SKDFB#V0, R5F101SLDFB#V0 R5F101SHDFB#X0, R5F101SJDFB#X0, R5F101SKDFB#X0, R5F101SLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

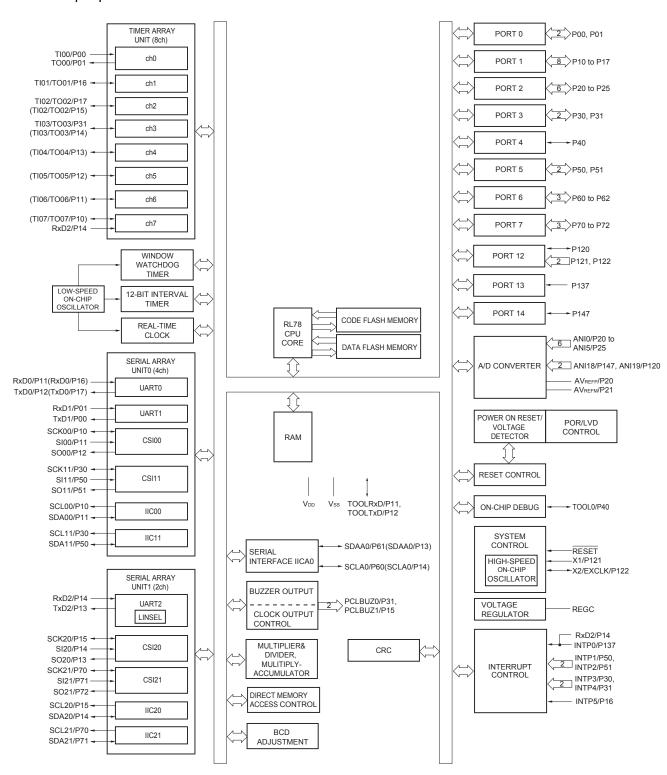
1.3.12 80-pin products

- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 x 12 mm, 0.5 mm pitch)



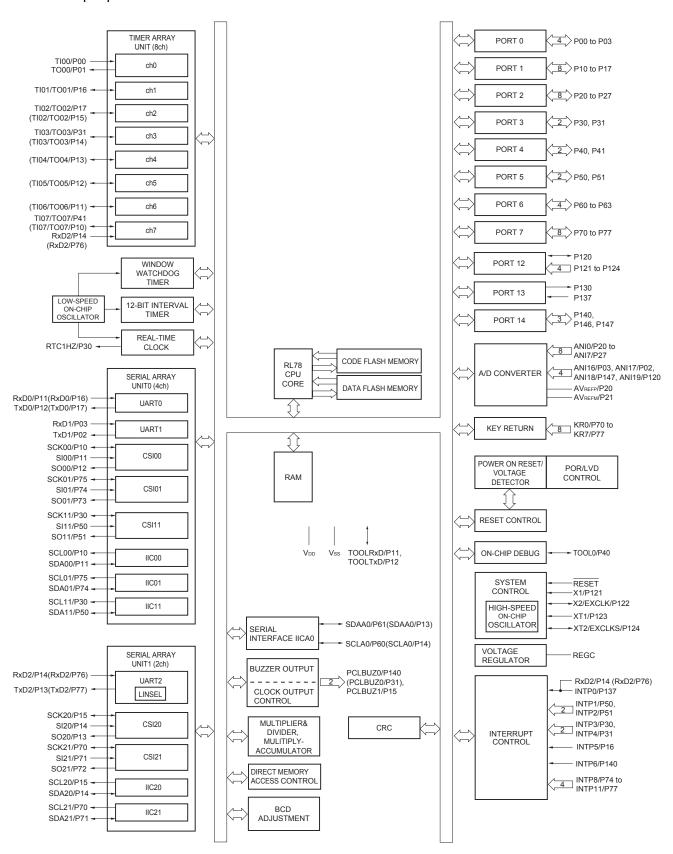
- Cautions 1. Make EVsso pin the same potential as Vss pin.
 - 2. Make VDD pin the potential that is higher than EVDDO pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the Vss and EV_{SS0} pins to separate ground lines.
 - **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.

1.5.6 36-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.5.10 52-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

3. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).

4. When setting to PIOR = 1

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Iter	Item			20-pin 24-pin				25-pin 30-pin		32-pin 36-pi			
i iii											İ		İ
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Clock output/buzze	er output	-	=		1		1		2		2		2
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation)											
8/10-bit resolution	A/D converter	6 chanr	nels	6 chanr	nels	6 chanr	nels	8 chanı	nels	8 chan	nels	8 chan	nels
Serial interface		[20-pin,	24-pin,	25-pin p	roducts]								
		• CSI:	1 chann	el/simplif	ied I ² C:	1 channe	el/UART	: 1 chanr	nel				
		• CSI:	1 chann	el/simplif	ied I ² C:	1 channe	el/UART	: 1 chanr	nel				
		[30-pin,	32-pin	products]]								
		• CSI:	1 chann	el/simplif el/simplif	ied I ² C:	1 channe	el/UART	: 1 chanr	nel				
				el/simplif	fied I ² C:	1 channe	el/UART	(UART s	supportir	ng LIN-b	us): 1 ch	nannel	
		[36-pin											
		1		el/simplif									
1		 CSI: 1 channel/simplified l²C: 1 channel/UART: 1 channel CSI: 2 channels/simplified l²C: 2 channels/UART (UART supporting LIN-bus): 1 channel 											
ſ	I ² C bus	-	=	1 chanr		1 chanr		1 chanı		1 chan		1 chan	nel
Multiplier and divide accumulator	er/multiply-	 16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 											
DMA controller		2 channels											
Vectored interrupt	Internal	2	3	2	24	2	<u>!</u> 4	2	27	2	27	2	27
sources	External	;	3	ļ	5		5		6		6		6
Key interrupt								•					
Reset													
		InterrInterrInterrInterrInterr	nal reset nal reset nal reset nal reset nal reset	SET pin by watch by power by volta by illega by RAM by illega	er-on-res ge detec al instruc parity e	et ctor tion exec rror		e					
Power-on-reset circ	puit	InterrInterrInterrInterrInterrInterrPowe	nal reset nal reset nal reset nal reset nal reset er-on-res	by watch by power by volta by illega by RAM by illega	er-on-res ge detect al instruct parity e al-memod	et stor stor tion exec rror ry access		0					
Power-on-reset circ	cuit	InterrInterrInterrInterrInterrInterrPowe	nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser er-down-	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detectal instruction parity et al-memorial.51 V (Tours) (et stor stor tion exec rror ry access	s 14 stage	es)					
		Interr Interr Interr Interr Interr Interr Interr Powe	nal reset nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser-down- g edge: g edge	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detectal instruction parity et al-memorial.51 V (Tours) (et ctor tion exec rror ry access YP.) YP.)	s 14 stage	es)					
Voltage detector	ction	Interresident In	nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser-down- g edge: g edge d	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detect al instruct parity e al-memon .51 V (T .50 V (T .67 V to	set stor rich execution ex	s 14 stage	es)					
Voltage detector On-chip debug fund	ction	 Interr Interr Interr Interr Interr Interr Powe Powe Rising Fallin Provide 	nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset gr-on-reser-down- g edge: g edge d	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detect al instruct parity e al-memon .51 V (T .50 V (T .67 V to .63 V to	set stor return execution exec	s 14 stage	es)					
Voltage detector On-chip debug fund	ction	 Interr Interr Interr Interr Interr Interr Interr Powe Powe Rising Fallin Provide V_{DD} = 1 V_{DD} = 2. 	nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser er-down- g edge g edge d .6 to 5.5	by watch by power by volta by illegate by RAM by illegate by illeg	er-on-res ge detect al instruct parity e al-memor .51 V (T .50 V (T .63 V to .63 V to	set stor rich execution ex	s 14 stage 14 stage	es)	applica	tions)			

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

[40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

	Item 40-pin 44-pin						·pin	52-pin		(1/2) 64-pin		
	item		<u> </u>	44	i			52-	-piri		İ	
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx	
		100	101	100	101	100	101	100	101	100	101	
		Ex	Ex	×	F _×	χ Ω	ωx	×	×	Ž	Ž	
Code flash me	emory (KB)	16 to	o 192	16 t	o 512	16 t	512	32 to	o 512	32 to	o 512	
Data flash me	emory (KB)	4 to 8	-	4 to 8	_	4 to 8	-	4 to 8	_	4 to 8	_	
RAM (KB)		2 to 1	16 ^{Note1}	2 to :	32 ^{Note1}	2 to 32 ^{Note1} 2 to 32 ^{Note1}				2 to 32 ^{Note1}		
Address space	e	1 MB										
Main system clock	High-speed system clock	HS (High HS (High LS (Low-	crystal/ceramic) oscillation, external main system clock input (EXCLK) (High-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), [Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), [Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)									
	High-speed on-chip oscillator	HS (High LS (Low-	(High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)									
Subsystem cl	ock		T1 (crystal) oscillation, external subsystem clock input (EXCLKS) 2.768 kHz									
Low-speed or	n-chip oscillator	15 kHz (TYP.)									
General-purp	ose registers	(8-bit reg	ister × 8)	× 4 banks								
Minimum insti	ruction execution time	0.03125	μs (High-s	speed on-	chip oscilla	tor: fin = 3	2 MHz op	eration)				
		0.05 <i>μ</i> s (High-spee	ed system	clock: fmx	= 20 MHz	operation)				
		30.5 μs (Subsyster	n clock: fs	ыв = 32.76	8 kHz ope	ration)					
Instruction se	t	AdderMultipl	ication (8	actor/logic bits × 8 bit	al operation ts) t manipula			and Book	ean opera	tion), etc.		
I/O port	Total	3	36	4	40	2	14	4	18	5	58	
	CMOS I/O	(N-ch (28 O.D. I/O ithstand ge]: 10)	(N-ch [V _{DD} w	31 O.D. I/O rithstand ge]: 10)	(N-ch (34 O.D. I/O ithstand je]: 11)	(N-ch (38 O.D. I/O ithstand ge]: 13)	(N-ch (18 O.D. I/O ithstand ge]: 15)	
	CMOS input		5		5		5		5		5	
	CMOS output		=		=		1		1		1	
	N-ch O.D. I/O (withstand voltage: 6 V)		3		4		4		4		4	
Timer	16-bit timer					8 cha	nnels					
	Watchdog timer					1 cha	annel					
	Real-time clock (RTC)					1 cha	annel					
	12-bit interval timer (IT)				-		annel					
	Timer output	outputs: 3 8 channels	t channels (PWM outputs: 4 Note 2), butputs: 3 Note 2), 8 channels (PWM outputs: 7 Note 2) Note 3 Outputs: 7 Note 2) Note 3 Outputs: 7 Note 2 Note 3 Outputs: 7 Note 3 Outputs: 7 Note 2 Note 3 Outputs: 7 Note 2 Note 3 Outputs: 7 Outputs: 7 Outputs: 7 Outputs: 7 Outputs: 7 Outputs: 7 Outputs: 7									
	RTC output	1 channe • 1 Hz (s		ı clock: fsu	ıв = 32.768	3 kHz)						

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = E to G, J, L): Start address FF300H R5F100xE, R5F101xE (x = E to G, J, L): Start address FEF00H R5F100xJ, R5F101xJ (x = F, G, J, L): Start address FAF00H R5F100xL, R5F101xL (x = F, G, J, L): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

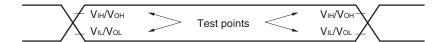
(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (1/2)

Parameter	Symbol			Conditions	,	_	MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating	HS (high-	fih = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		2.6		mA
current		mode	speed main) mode Note 5		operation	$V_{DD} = 3.0 \text{ V}$		2.6		mA
					Normal	$V_{DD} = 5.0 \text{ V}$		6.1	9.5	mA
					operation	$V_{DD} = 3.0 \text{ V}$		6.1	9.5	mA
				$f_{IH} = 24 \text{ MHz}^{Note 3}$	Normal	$V_{DD} = 5.0 \text{ V}$		4.8	7.4	mA
					operation	$V_{DD} = 3.0 \text{ V}$		4.8	7.4	mA
				$f_{IH} = 16 \text{ MHz}^{Note 3}$	Normal	$V_{DD} = 5.0 \text{ V}$		3.5	5.3	mA
					operation	$V_{DD} = 3.0 \text{ V}$		3.5	5.3	mA
			LS (low-	$f_{IH} = 8 \text{ MHz}^{Note 3}$	Nomal	$V_{DD} = 3.0 \text{ V}$		1.5	2.3	mA
			speed main) mode Note 5		operation	V _{DD} = 2.0 V		1.5	2.3	mA
			LV (low-	$f_{IH} = 4 \text{ MHz}^{\text{Note 3}}$	Normal	V _{DD} = 3.0 V		1.5	2.0	mA
	voltage main) mode		operation	V _{DD} = 2.0 V		1.5	2.0	mA		
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.9	6.1	mA
		speed main) mode Note 5	$V_{DD} = 5.0 \text{ V}$	operation	Resonator connection		4.1	6.3	mA	
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.9	6.1	mA
		$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		4.1	6.3	mA		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.5	3.7	mA
				$V_{DD} = 5.0 \text{ V}$	operation	Resonator connection		2.5	3.7	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		2.5	3.7	mA
				$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		2.5	3.7	mA
			LS (low-	$f_{MX} = 8 MHz^{Note 2}$	Nomal	Square wave input		1.4	2.2	mA
			speed main) mode Note 5	$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		1.4	2.2	mA
				$f_{MX} = 8 MHz^{Note 2}$	Nomal	Square wave input		1.4	2.2	mA
				$V_{DD} = 2.0 \text{ V}$	operation	Resonator connection		1.4	2.2	mA
			Subsystem	fsub = 32.768 kHz	Nomal	Square wave input		5.4	6.5	μΑ
			clock operation	T _A = -40°C	operation	Resonator connection		5.5	6.6	μΑ
				fsub = 32.768 kHz	Nomal	Square wave input		5.5	6.5	μΑ
				T _A = +25°C	operation	Resonator connection		5.6	6.6	μΑ
				fsub = 32.768 kHz	Nomal	Square wave input		5.6	9.4	μΑ
				TA = +50°C	operation	Resonator connection		5.7	9.5	μΑ
				fsuB = 32.768 kHz	Normal	Square wave input		5.9	12.0	μΑ
				Note 4 $T_A = +70^{\circ}C$	operation	Resonator connection		6.0	12.1	μΑ
				fsuв = 32.768 kHz	Normal	Square wave input		6.6	16.3	μΑ
				Note 4 $T_A = +85^{\circ}C$	operation	Resonator connection		6.7	16.4	μΑ

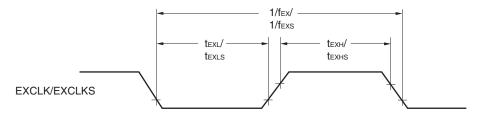
(Notes and Remarks are listed on the next page.)



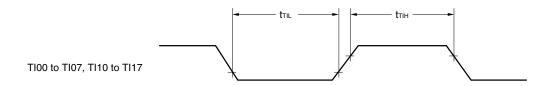
AC Timing Test Points

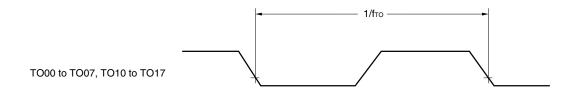


External System Clock Timing

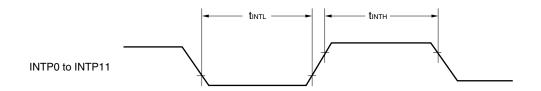


TI/TO Timing

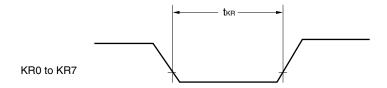




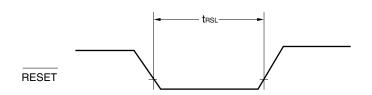
Interrupt Request Input Timing



Key Interrupt Input Timing



RESET Input Timing



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

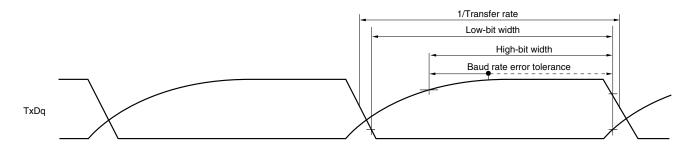
(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

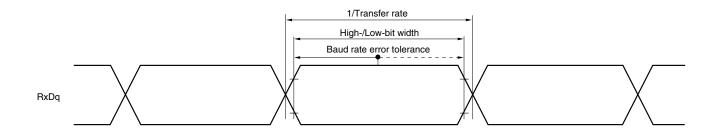
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Condit	Conditions			LS (low	r-speed Mode	LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCKp cycle time			20 MHz < fмск	8/fмск				_		ns
Note 5		V	fмcк ≤ 20 MHz	6/fмск		6/ƒмск		6/ƒмск		ns
		$2.7~V \leq EV_{DD0} \leq 5.5$	16 MHz < fмск	8/fмск		_		_		ns
		V	fмcк ≤ 16 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.4~V \le EV_{DD0} \le 5.5~V$		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
	$1.8~V \leq EV_{DD0} \leq 5.5~V$			6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5	V	_		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tkH2,	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 7		tксү2/2 - 7		tксү2/2 - 7		ns
		$2.7~\text{V} \leq \text{EV}_\text{DD0} \leq 5.5~\text{V}$		tксу2/2 — 8		tксу2/2 - 8		tксу2/2 - 8		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 18		tксу2/2 - 18		tксу2/2 - 18		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 66		tксү2/2 - 66		tксү2/2 - 66		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5	V	_		tkcy2/2 - 66		tkcy2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)

UART mode bit width (during communication at different potential) (reference)





- $\begin{tabular}{ll} \begin{tabular}{ll} \bf R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (hig	h-speed Mode	`	r-speed Mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$\begin{split} 4.0 \ V & \le EV_{DD0} \le 5.5 \ V, \\ 2.7 \ V & \le V_b \le 4.0 \ V, \\ C_b & = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{split}$	300		1150		1150		ns
			$\begin{split} 2.7 \ V & \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	500		1150		1150		ns
			$\begin{aligned} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{Note}, \end{aligned}$	1150		1150		1150		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \le \text{EV}_{DD}$ $2.7 \text{ V} \le \text{V}_{b} \le \text{C}_{b} = 30 \text{ pF},$	4.0 V,	tксү1/2 – 75		tксү1/2 – 75		tксу1/2 — 75		ns
		$2.7 \text{ V} \le \text{EV}_{DD}$ $2.3 \text{ V} \le \text{V}_{b} \le$ $C_{b} = 30 \text{ pF},$	00 < 4.0 V, 2.7 V,	tксу1/2 — 170		tксу1/2 — 170		tксу1/2 — 170		ns
		$1.8 \text{ V} \le \text{EV}_{DD}$ $1.6 \text{ V} \le \text{V}_{b} \le \text{C}_{b} = 30 \text{ pF},$	00 < 3.3 V, 2.0 V ^{Note} ,	tксү1/2 – 458		tксү1/2 – 458		tксү1/2 – 458		ns
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq$	00 ≤ 5.5 V, 4.0 V,	tксу1/2 — 12		tксү1/2 — 50		tксү1/2 — 50		ns
		$C_b = 30 \text{ pF},$ $2.7 \text{ V} \leq \text{EVor}$ $2.3 \text{ V} \leq \text{V}_b \leq$ $C_b = 30 \text{ pF},$	00 < 4.0 V, 2.7 V,	tксү1/2 — 18		tксү1/2 — 50		tксү1/2 — 50		ns
		$1.8 \text{ V} \leq \text{EV}_{DD}$ $1.6 \text{ V} \leq \text{V}_{b} \leq$ $C_{b} = 30 \text{ pF},$	00 < 3.3 V, 2.0 V ^{Note} ,	tксү1/2 — 50		tксү1/2 – 50		tксу1/2 — 50		ns

Note Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

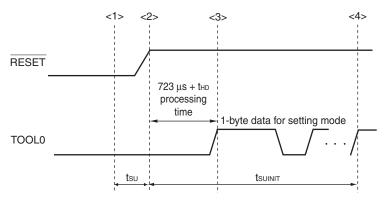
- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.
 - Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD} .
 - Zero-scale error/Full-scale error: Add $\pm 0.05\%FSR$ to the MAX. value when AV_{REFP} = V_{DD}.
 - Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 - **4.** Values when the conversion time is set to 57 μ s (min.) and 95 μ s (max.).
 - 5. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.



2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuіліт	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to +105°C R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
 - 4. Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^{\circ}C$ to $+105^{\circ}C$. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of $T_A = -40$ to +85°C, see CHAPTER 2 ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +85°C).

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^{\circ}$ C)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Ар	plication
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0} 1 \text{ MHz to } 32 \text{ MHz}$ $2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0} 1 \text{ MHz to } 16 \text{ MHz}$ $LS \text{ (low-speed main) mode:}$ $1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0} 1 \text{ MHz to } 8 \text{ MHz}$ $LV \text{ (low-voltage main) mode:}$ $1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0} 1 \text{ MHz to } 4 \text{ MHz}$	HS (high-speed main) mode only: $2.7~V \le V_{DD} \le 5.5~V @ 1~MHz~to~32~MHz$ $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz~to~16~MHz$
High-speed on-chip oscillator clock accuracy	1.8 V \leq V _{DD} \leq 5.5 V \pm 1.0%@ TA = -20 to +85°C \pm 1.5%@ TA = -40 to -20°C 1.6 V \leq V _{DD} $<$ 1.8 V \pm 5.0%@ TA = -20 to +85°C \pm 5.5%@ TA = -40 to -20°C	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ $\pm 2.0\%@ \text{ T}_{A} = +85 \text{ to } +105^{\circ}\text{C}$ $\pm 1.0\%@ \text{ T}_{A} = -20 \text{ to } +85^{\circ}\text{C}$ $\pm 1.5\%@ \text{ T}_{A} = -40 \text{ to } -20^{\circ}\text{C}$
Serial array unit	UART CSI: fclk/2 (supporting 16 Mbps), fclk/4 Simplified I ² C communication	UART CSI: fclk/4 Simplified I ² C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

(Remark is listed on the next page.)



 $(T_A = -40 \text{ to } +105^{\circ}\text{C}. 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}. \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	EV _{DD0} – 0.7			V
		P90 to P97, P100 to P106, P110 to	$\label{eq:loss_problem} \begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \\ \text{I}_{\text{OH1}} = -2.0 \ \text{mA} \end{array}$	EV _{DD0} – 0.6			V
V _{OH2}		P117, P120, P125 to P127, P130, P140 to P147	$2.4~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OH1} = -1.5~mA$	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \ \mu \text{ A}$	V _{DD} – 0.5			V
Output voltage, low		P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 8.5~mA$			0.7	V
		to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 3.0~mA$			0.6	V
			$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 1.5~mA$			0.4	V
			$2.4~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 0.6~mA$			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	2.4 V \leq V _{DD} \leq 5.5 V, I _{OL2} = 400 μ A			0.4	V
	Vоьз	P60 to P63	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 15.0~mA$			2.0	V
			$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 5.0~mA$			0.4	V
			$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 3.0~mA$			0.4	V
			$2.4~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 2.0~mA$			0.4	V

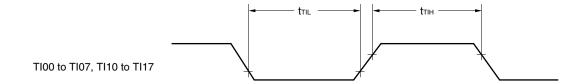
Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

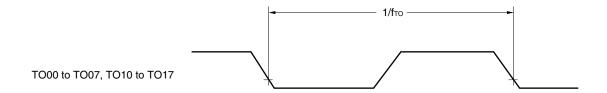
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

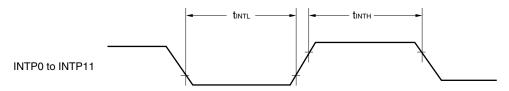
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

TI/TO Timing

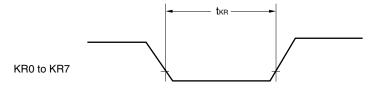




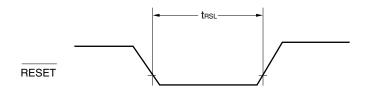
Interrupt Request Input Timing



Key Interrupt Input Timing



RESET Input Timing



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-spee	d main) Mode	Unit
					MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	250		ns
			$2.4~V \leq EV_{DD0} \leq 5.5~V$	500		ns
SCKp high-/low-level width	t кн1,	4.0 V ≤ EV _{DD}	₀ ≤ 5.5 V	tксү1/2 – 24		ns
	t _{KL1}	2.7 V ≤ EV _{DD}	0 ≤ 5.5 V	tkcy1/2 - 36		ns
		2.4 V ≤ EV _{DD}	₀ ≤ 5.5 V	tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsıĸı	4.0 V ≤ EV _{DD}	₀ ≤ 5.5 V	66		ns
		2.7 V ≤ EV _{DD}	0 ≤ 5.5 V	66		ns
		2.4 V ≤ EV _{DD}	₀ ≤ 5.5 V	113		ns
SIp hold time (from SCKp↑) Note 2	t KSI1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note	04		50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3).
 - g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 - n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (simplified I²C mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-sp Mo	,	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7~V \leq EV_{DD0} \leq 5.5~V,$		400 Note1	kHz
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$		100 Note1	kHz
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "L"	tLOW	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1200		ns
		$C_b = 50$ pF, $R_b = 2.7$ k Ω			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "H"	tніgн	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1200		ns
		$C_b = 50$ pF, $R_b = 2.7$ k Ω			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Data setup time (reception)	tsu:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1/fmck + 220		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	Note2		
		$2.4~V \leq EV_{DD} \leq 5.5~V,$	1/fмск + 580		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	Note2		
Data hold time (transmission)	thd:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	0	770	ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	0	1420	ns
		$C_b = 100 \ pF, \ R_b = 3 \ k\Omega$			

Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

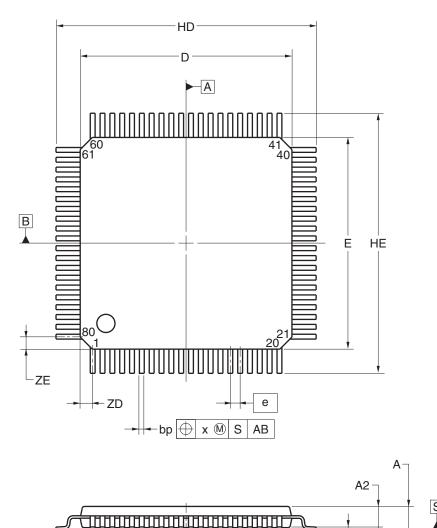
Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

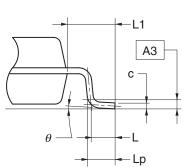
4.12 80-pin Products

R5F100MFAFA, R5F100MGAFA, R5F100MHAFA, R5F100MJAFA, R5F100MKAFA, R5F100MLAFA R5F101MFAFA, R5F101MGAFA, R5F101MHAFA, R5F101MJAFA, R5F101MKAFA, R5F101MLAFA R5F100MFDFA, R5F100MGDFA, R5F100MHDFA, R5F100MJDFA, R5F100MKDFA, R5F101MLDFA R5F101MFDFA, R5F101MGDFA, R5F101MHDFA, R5F101MJDFA, R5F101MKDFA, R5F101MLDFA R5F100MFGFA, R5F100MGGFA, R5F100MHGFA, R5F100MJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69



S



detail of lead end

Referance	Dimension in Millimeters				
Symbol	Min	Nom	Max		
D	13.80	14.00	14.20		
Е	13.80	14.00	14.20		
HD	17.00	17.20	17.40		
HE	17.00	17.20	17.40		
Α			1.70		
A1	0.05	0.125	0.20		
A2	1.35	1.40	1.45		
A3		0.25			
bp	0.26	0.32	0.38		
С	0.10	0.145	0.20		
L		0.80			
Lp	0.736	0.886	1.036		
L1	1.40	1.60	1.80		
θ	0°	3°	8°		
е		0.65			
х			0.13		
У			0.10		
ZD		0.825			
ZE		0.825			

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